

## FP-1310HP10-C

## 1.31µm 10G FP Laser Chip

## Features

- 10G operation - Operation temperature: -40°C – 85°C - AlInGaAs MQW design - Proven reliability

## Specification

Item	Symbol	Minimum	Typical	Maximum	Unit	Conditions
Centre wavelength	$\lambda_c$		1310		nm	25°C, 50mA
Threshold current	$I_{th25}$		8.5	12	mA	25°C
	$I_{th85}$		17	22	mA	85°C
$T_{zero}$	$T_0$		85		K	25°C -85°C
Operation Current	$I_{op25}$		25	30	mA	5mW, 25°C
	$I_{op85}$		36	41	mA	5mW, 85°C
Operation Voltage	$V_{op25}$		1.15	1.4	V	25°C
	$V_{op85}$		1.20	1.6	V	85°C
Slope Efficiency	$dL/dI_{25}$	0.26	0.30		mW/mA	$I_{th}+5mA$ , 25°C
	$dL/dI_{85}$	0.20	0.25		mW/mA	$I_{th}+5mA$ , 85°C
Resistance	R		7	12	ohm	25°C, 50mA
RMS Spectral Width	$\lambda_{RMS}$		2	3	nm	25°C, 50mA
$d\lambda/dt$	$d\lambda/dt$		0.5	0.55	nm/C	25°C -85°C
Modulation bandwidth		10	14		GHz	25°C, $I_{th}+50mA$
Horizontal divergence angle	$\theta_{  }$		21		deg	50mA, FWHM
Vertical divergence angle	$\theta_{\perp}$		32			50mA, FWHM
Length	L	245	250	255	µm	
Width	W	195	200	205	µm	
thickness	T	95	100	105	µm	

## Absolute Maximum ratings

Item	Symbol	Min	Max	Unit
Operation temperature	$T_{op}$	-40	85	°C
Laser Forward Current	$I_F$		150	mA
Laser Reverse Voltage	$V_R$		2	V
Storage temperature	$T_S$	-50	100	°C
Solder temperature	$T_s$		320	°C

